

**GaAs Transfer Switch,
DC-3.0 GHz**

**SW-283-PIN
V4**

Features

- Small Ceramic Package, 0.250" Sq.
- Fast Switching Speed, 4 ns Typical
- Ultra Low DC Power Consumption
- 50 Ohm Nominal Impedance
- MIL-STD-883 screening available
- Lead-Free CR-4 Package
- 260°C Reflow Compatible

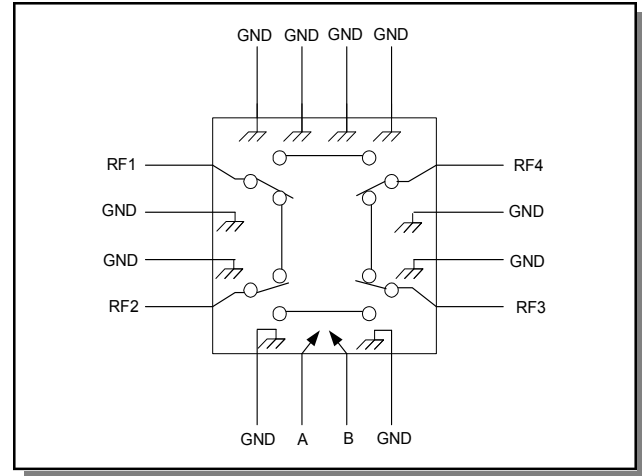
Description

M/A-COM's SW-283-PIN is a GaAs MMIC transfer switch packaged in lead-free, surface mount CR-4 ceramic style packages. SW-283-PIN offers low insertion loss, high isolation, and fast switching. This ceramic switch platform has a common footprint for all three designs. The CR-4 package is hermetically sealed, making this switch ideal for space, military radios, and other environmentally harsh applications.

Typical applications include synthesizer switching, transmit/receive switching, switch matrices and filter banks in systems such as radio and cellular equipment, PCM, GPS, and fiber optic modules.

The SW-283-PIN transfer switch contains a monolithic GaAs MMIC which is fabricated using a 1.0 micron MESFET process.

Functional Block Diagram



Ordering Information

Part Number	Package
SW-283-PIN	Bulk Packaging

Note: Reference Application Note M513 for reel size information.

Note: Die quantity varies.

Pin Configuration

Pin No.	Function	Pin No.	Function
1	RF1	9	RF3
2	GND	10	GND
3	GND	11	GND
4	RF2	12	RF4
5	GND	13	GND
6	A	14	GND
7	B	15	GND
8	GND	16	GND

The metal bottom of the case must be connected to RF and DC ground.

* Restrictions on Hazardous Substances, European Union Directive 2002/95/EC.

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Electrical Specifications: $T_A = 25^\circ\text{C}$, $Z_0 = 50\Omega$ ^{1,2}

Parameter	Test Conditions	Frequency	Units	Min	Typ	Max
Insertion Loss	—	DC - 3 GHz	dB	—	—	2.1
		DC - 2 GHz	dB	—	—	1.8
		DC - 1 GHz	dB	—	—	1.3
		DC - 0.5 GHz	dB	—	—	1.0
VSWR	—	DC - 3 GHz	Ratio	—	—	1.9:1
		DC - 2 GHz	Ratio	—	—	1.7:1
		DC - 1 GHz	Ratio	—	—	1.3:1
		DC - 0.5 GHz	Ratio	—	—	1.25:1
Isolation	—	DC - 3 GHz	dB	20	—	—
		DC - 2 GHz	dB	25	—	—
		DC - 1 GHz	dB	40	—	—
		DC - 0.5 GHz	dB	45	—	—
Trise, Tfall Ton, Toff Transients	10/90% or 90/10% RF 50% CTL to 90/10% RF In-Band	—	nS	—	2	—
		—	nS	—	4	—
		—	mV	—	30	—
1 dB Compression	Control Voltage 0/-5 VDC	0.5 - 3 GHz	dBm	—	+27	—
		0.05 GHz	dBm	—	+21	—
	Control Voltage 0/-8 VDC	0.5 - 3 GHz	dBm	—	+33	—
		0.05 GHz	dBm	—	+26	—
IP ₂	For two-tone Input power up to +13 dBm	0.5 - 3 GHz	dBm	—	+68	—
		0.05 GHz	dBm	—	+62	—
IP ₃	For two-tone Input power up to +13 dBm	0.5 - 3 GHz	dBm	—	+50	—
		0.05 GHz	dBm	—	+45	—
Control Voltages	V _{IN} Low: 0 to -0.2V V _{IN} High: -5V @ 10 μ A Typ to -8V	— —	— —	— —	— —	5 μ A 200 μ A

1. All specifications apply with 50 ohm impedance connected to all RF ports with 0 and -5 VDC control voltages.
2. Faster switching speed can be achieved with enhanced driver waveform.

Absolute Maximum Ratings ^{3,4}

Parameter	Absolute Maximum
Input Power 0.05 GHz 0.5 - 3.0 GHz	+27 dBm +34 dBm
Control Voltage	-8.5 V \leq V _c \leq +5 V
Operating Temperature	-55°C to +125°C
Storage Temperature	-65°C to +150°C

3. Exceeding any one or combination of these limits may cause permanent damage to this device.
4. M/A-COM does not recommend sustained operation near these survivability limits.

Handling Procedures

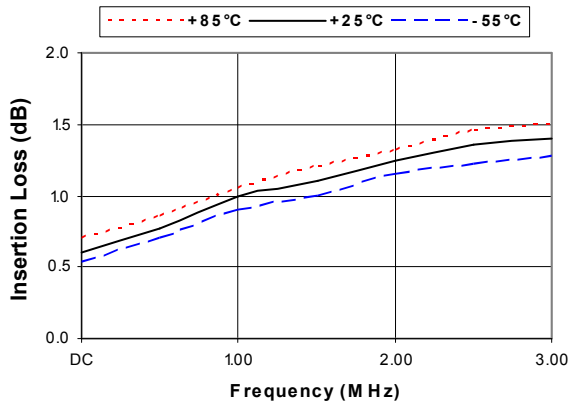
Please observe the following precautions to avoid damage:

Static Sensitivity

Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

Typical Performance Curves

Insertion Loss vs. Frequency

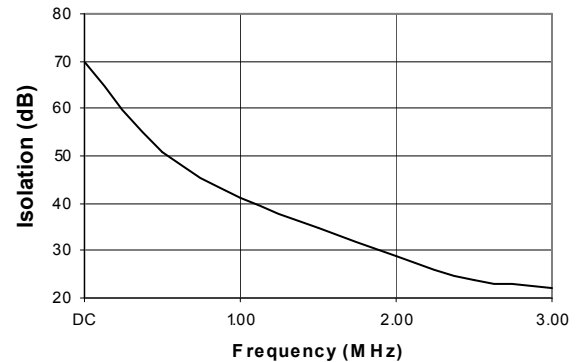


Truth Table (Switch)

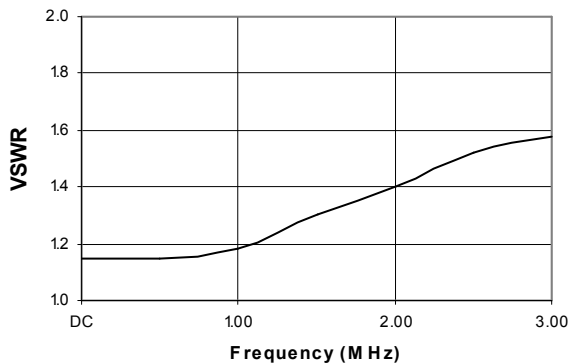
Control Input		Condition of Switch			
A	B	RF1- RF2	RF2- RF3	RF1- RF4	RF3- RF4
HI	LOW	OFF	ON	ON	OFF
LOW	HI	ON	OFF	OFF	ON

Low = 0.0V, High = -5.0V

Isolation vs. Frequency



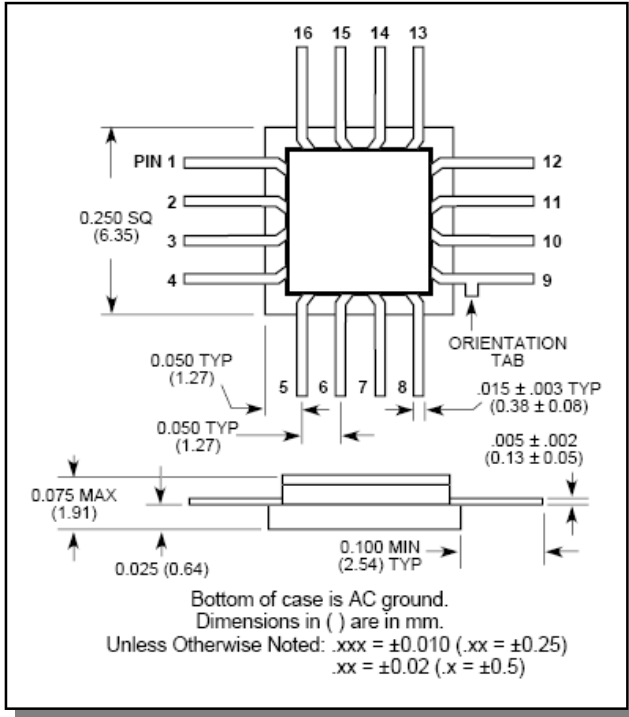
VSWR vs. Frequency



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Lead-Free, CR-4 Ceramic Package[†]



[†] Reference Application Note M538 for lead-free solder reflow recommendations.